AUTOMOTIVE

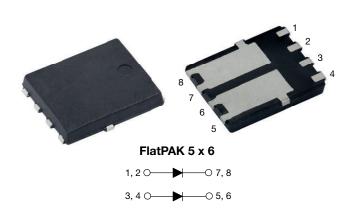
ROHS

HALOGEN FREE



Vishay Semiconductors

Hyperfast Rectifier, 2 x 3 A FRED Pt®



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS							
Package FlatPAK 5 x 6							
I _{F(AV)}	2 x 3 A						
V _R	200 V						
V _F at I _F	0.71 V						
t _{rr (typ.)}	25 ns						
T _J max.	175 °C						
Circuit configuration	Separated cathode						

FEATURES

- Hyperfast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- Specific for output and snubber operation
- Low forward voltage drop
- Low leakage current
- AEC-Q101 qualified
- Meets MSL level 1 per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, piezo-injection, as high frequency rectifiers, and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

MECHANICAL DATA

Case: FlatPAK 5 x 6

Molding compound meets UL 94 V-0 flammability rating

Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per

J-STD-002, meets JESD 201 class 2 whisker test

ABSOLUTE MAXIMUM RATINGS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage		V _{RRM}		200	V		
Average rectified forward current	per	I _{F(AV)}	T _{Solderpad} = 170 °C, DC	- 6			
	device		T _{Solderpad} = 169 °C, D = 0.5				
Non-repetitive peak surge current	per device	I _{ESM}	T _{.I} = 25 °C, 10 ms sinusoidal pulse	173	А		
	per diode	. 5	,	87			
Operating junction and storage temperatures		T _J , T _{Stg}		-55 to +175	°C		



www.vishay.com

Vishay Semiconductors

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER SYMBOL TEST CONDITIONS MIN. TYP. MAX. UNITS								
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-	.,		
Forward voltage, per diode	V _F	I _F = 3 A	-	0.88	0.94	V		
		I _F = 3 A, T _J = 150 °C	-	0.71	0.74			
Reverse leakage current, per diode	I _R	V _R = V _R rated	-	-	2			
		$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	2	40	μA		
Junction capacitance	C _T	V _R = 200 V	-	14	-	pF		

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time		$I_F = 1.0 \text{ A, } dI_F/dt =$	= 50 A/ μ s, V _R = 30 V	ı	20	-			
	+	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$		ı	-	25	no		
	t _{rr}	T _J = 25 °C		-	15	-	ns		
		T _J = 125 °C		-	25	-			
Dook recovery current	I _{RRM}	T _J = 25 °C	$I_F = 3 A$	=	2	-	Α		
Peak recovery current		T _J = 125 °C	dl _F /dt = 200 A/μs V _B = 160 V	-	3	-			
Reverse recovery charge	Q _{rr}	T _J = 25 °C]	ı	12	-	nC		
		T _J = 125 °C		-	40	-	110		

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C			
Thermal resistance, junction to ambient, per diode	R _{thJA} (1)(2)		-	90	103	°C/W			
Thermal resistance, junction to mount, per diode	R _{thJM} (3)		-	2.3	2.6	C/VV			

Notes

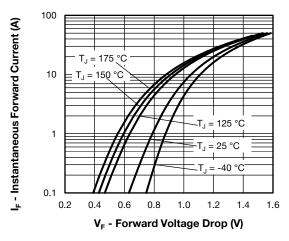
 $^{^{(1)}}$ The heat generated must be less than the thermal conductivity from junction to ambient: $dP_D/dT_J < 1/P_{thJA}$

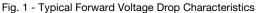
 $^{^{(2)}}$ Free air, mounted or recommended copper pad area; thermal resistance R_{thJA} - junction to ambient

⁽³⁾ Mounted on infinite heatsink



Vishay Semiconductors





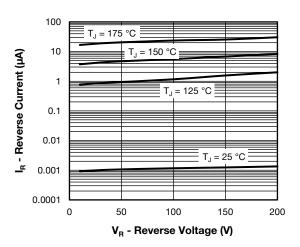


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

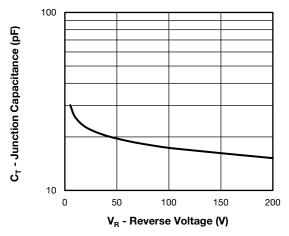


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

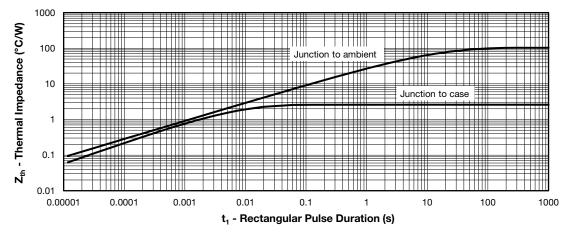


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

www.vishay.com

Vishay Semiconductors

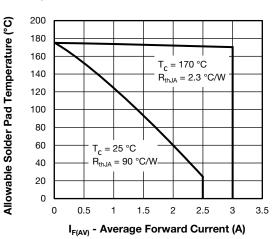
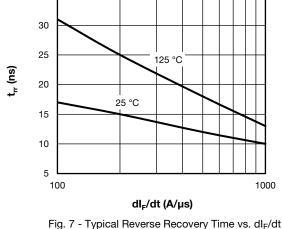


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current



35

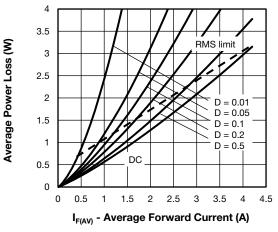


Fig. 6 - Forward Power Loss Characteristics

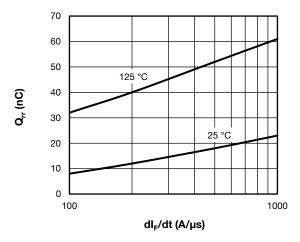
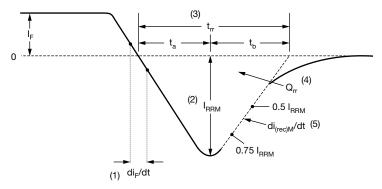


Fig. 8 - Typical Stored Charge vs. dl_F/dt



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during tb portion of tr

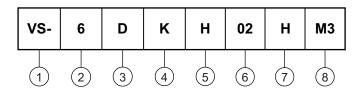
Fig. 9 - Reverse Recovery Waveform and Definitions



Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

2 - Current rating (6 = 6 A)

3 - Circuit configuration:

D = separated cathode

4 - K = FlatPAK package

5 - Process type,

H = hyperfast recovery

• Voltage code (02 = 200 V)

7 - H = AEC-Q101 qualified

8 - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

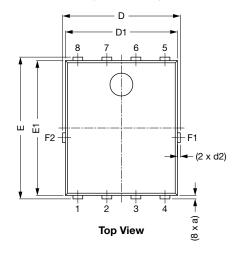
ORDERING INFORMATION (example)								
PREFERRED P/N	UNIT WEIGHT (g) PREFERRED PACKAGE CODE BASE QUANTITY PACKAGING DESCRIPTION							
VS-6DKH02HM3/H	0.10	Н	1500	7"diameter plastic tape and reel				

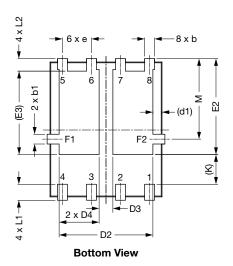
LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?96056					
Part marking information	www.vishay.com/doc?96059					
Packaging information	www.vishay.com/doc?88869					
SPICE model	www.vishay.com/doc?96882					

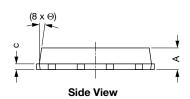
Vishay Semiconductors

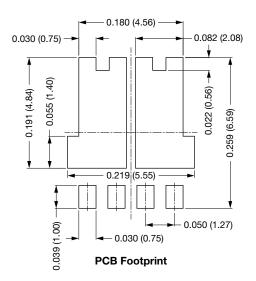
FlatPAK 5 x 6 (Dual)

DIMENSIONS in inches (millimeters)









DIM		INCHES			MILLIMETERS	METERS	
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	0.035	0.039	0.043	0.89	0.99	1.09	
(a)	-	0.006	-	-	0.15	-	
b	0.013	0.017	0.020	0.32	0.43	0.52	
b1	0.013	0.017	0.020	0.32	0.43	0.52	
С	0.008	-	0.014	0.20	-	0.35	
D	0.197	0.203	0.209	5.00	5.15	5.30	
D1	0.189	0.193	0.197	4.80	4.90	5.00	
D2	0.154	0.161	0.169	3.90	4.10	4.30	
D3	0.020	0.024	0.031	0.50	0.60	0.80	
D4	0.063	0.069	0.075	1.60	1.75	1.90	
(d1)	-	0.016	-	=	0.40	=	
(d2)	-	0.005	-	-	0.125	-	
Е	0.238	0.244	0.250	6.05	6.20	6.35	



Outline Dimensions

www.vishay.com

Vishay Semiconductors

DIM.		INCHES			MILLIMETERS		
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
E1	0.228	0.232	0.236	5.80	5.90	6.00	
E2	0.157	0.165	0.173	4.00	4.20	4.40	
(E3)	-	0.144	=	-	3.65	=	
е		0.050 BSC			1.27 BSC		
(K)	0.039	-	-	1.00	-	-	
L1	0.019	-	0.043	0.48	-	1.10	
L2	0.012	-	0.031	0.30	-	0.80	
M	0.128	0.138	0.148	3.25	3.50	3.75	
Θ	0°	-	10°	0°	-	10°	

Notes

- Dimensioning and tolerancing per ASME Y14.5-2009
- Dimensions D1 and E1 do not include mold flash or gate burrs
- Dimension (XX) means reference only



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.